

Applic. No. : 09/816,923

In the Specification:

Replace the paragraph on page 14, line 23, through page 15,
line 10, with --

Then, a second conductive diffusion barrier layer is deposited, which covers the surface of the second insulating layer 8, the spacers 11' and the exposed surface of the first conductive structure 6. The second conductive diffusion barrier layer is formed of TaN, in a layer thickness of 10 nm to 50 nm, by means of PVD or CVD deposition. By depositing a further copper layer, which fills up the remaining clearance in the contact hole 10, and structuring the copper layer and the second conductive diffusion barrier layer arranged underneath it, a second diffusion barrier structure 12 and a second conductive structure 13 are formed, the latter being conductively connected to the first conductive structure 6 (see Fig. 5). The second conductive structure 13 is configured as a conductor track belonging to a metalization plane. --